

DCR1575SY

Phase Control Thyristor

Replaces January 2000 version, DS4401-4.0

DS4401 -5.0 July 2001

FEATURES

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V V	Conditions
DCR1575SY42	4200	$T_{yi} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1575SY40	4000	$I_{DRM}^{v_J} = I_{RRM} = 500 \text{mA},$
DCR1575SY38	3800	V_{DRM} , V_{RRM} $t_p = 10ms$,
DCR1575SY36	3600	V_{DSM} & V_{RSM} =
DCR1575SY34	3400	V _{DRM} & V _{RRM} + 100V
DCR1575SY32	3200	respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1575SY36

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

V_{DRM} 4200V I_{T(AV)} 2536A I_{TSM} 44000A dVdt* 1000V/μs dI/dt 300A/μs

^{*}Higher dV/dt selections available

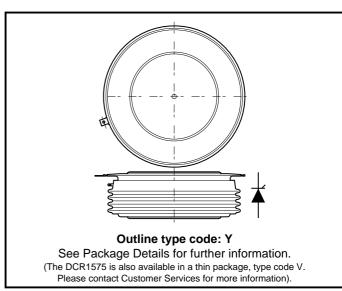


Fig. 1 Package outline



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	2536	Α			
I _{T(RMS)}	RMS value	-	3983	Α			
I _T	Continuous (direct) on-state current	-	3729	А			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1680	Α			
I _{T(RMS)}	RMS value	-	2639	А			
I _T	Continuous (direct) on-state current	-	2295	Α			

CURRENT RATINGS

T_{case} = 80°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	2010	А			
I _{T(RMS)}	RMS value	-	3155	А			
Ι _τ	Continuous (direct) on-state current	-	2850	А			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1310	А			
I _{T(RMS)}	RMS value	-	2050	А			
I _T	Continuous (direct) on-state current	-	1740	Α			



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	35.0	kA
l ² t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	6.13 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	44.0	kA
l²t	I ² t for fusing	V _R = 0	9.68 x 10 ⁶	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	Double side cooled	dc	-	0.0095	°C/W
		Single side cooled	Anode dc	-	0.019	°C/W
			Cathode dc	-	0.019	°C/W
R _{th(c-h)}		Clamping force 50.0kN with mounting compound	Double side	-	0.002	°C/W
			Single side	-	0.004	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	150	°C
-	Clamping force			45.0	55.0	kN



DYNAMIC CHARACTERISTICS

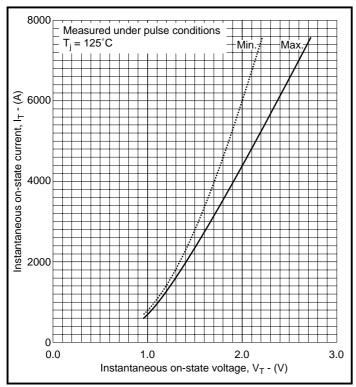
Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	300	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% $V_{DRM} T_j = 125^{\circ}C$.		-	1000	V/μs
-11/-14	F	Gate source 20V, 20Ω -	Repetitive 50Hz	-	150	A/μs
dl/dt	Rate of rise of on-state current		Non-repetitive	-	300	A/μs
$V_{T(TO)}$	Threshold voltage	At T _{vj} = 125°C		-	0.94	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.24	mΩ
t _{gd}	Delay time	$V_D = 67\% \ V_{DRM}$, Gate source 30V, 15 Ω Rise time 0.5 μ s, $T_j = 25^{\circ}$ C		-	2.5	μs
I _L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		550	1000	mA
I _H	Holding current	$T_j = 25^{\circ}C, R_{g-k} = \infty$		150	300	mA
t _q	Turn-off time	$I_{T} = 800A, t_{p} = 1 ms, T_{j} = 125 ^{\circ}C,$ $V_{RM} = 50V, dI_{RR}/dt = 20A/\mu s,$ $V_{DR} = 67\% V_{DRM}, dV_{DR}/dt = 20V/\mu s linear$		1.2	-	ms

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.0	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	300	mA
$V_{\rm GD}$	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	А
P _{GM}	Peak gate power	See table, gate characteristics curve	150	W
P _{G(AV)}	Mean gate power		10	W



CURVES



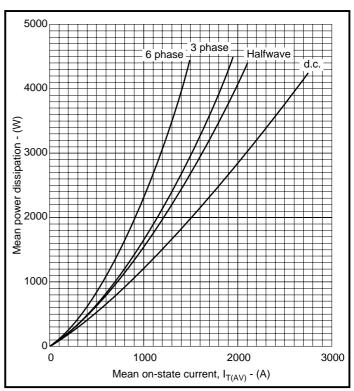


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Dissipation curves

 V_{TM} Equation:-

 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 1.659647

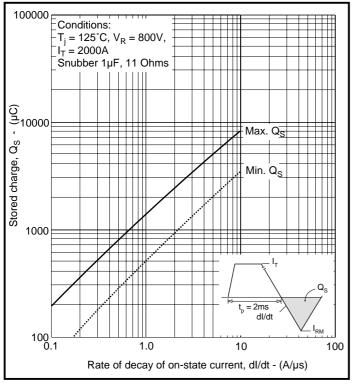
B = -0.2206499

 $C = 7.427997 \times 10^{-5}$

D = 0.02837417

these values are valid for $T_i = 125^{\circ}C$ for $I_T 500A$ to 7600A





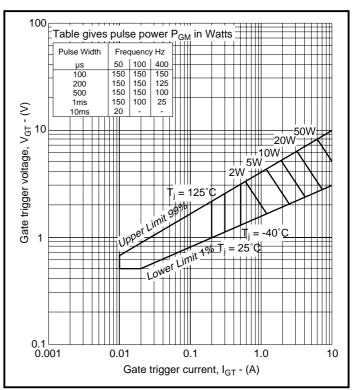


Fig.4 Stored charge

Fig.5 Gate characteristics

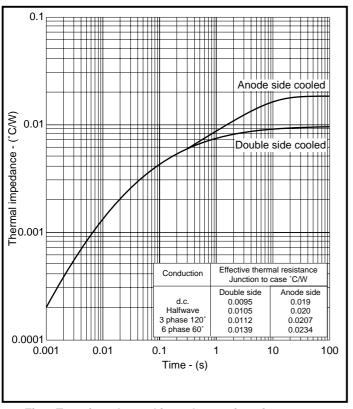


Fig.6 Transient thermal impedance - junction to case

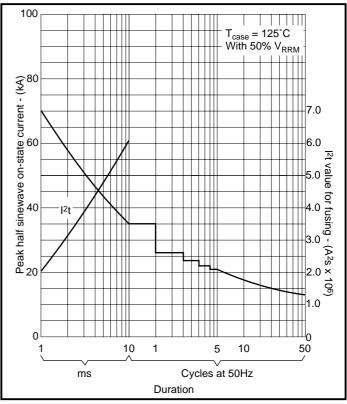
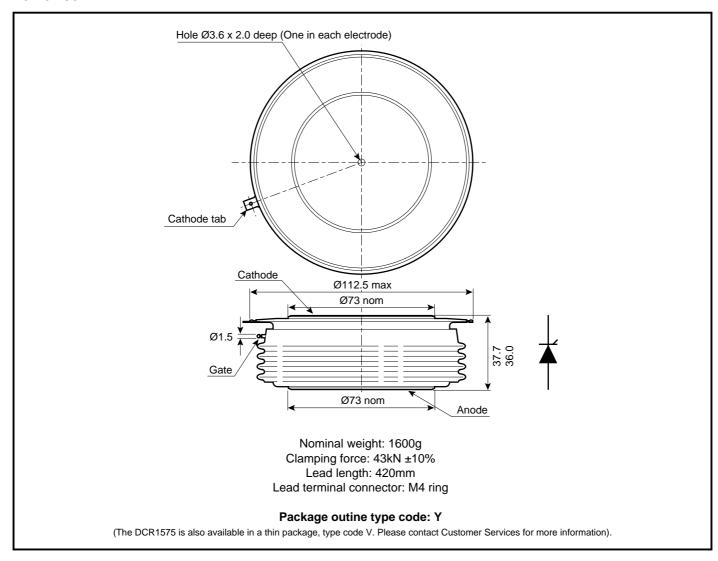


Fig.7 Surge (non-repetitive) on-state current vs time (with 50% $\rm V_{RRM}$ at $\rm T_{case}$ = 125°C)



PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

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